



# Extreme surface area microchannel plate device fabricated with ALD

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## Microchannel Plate Overview

### Very Fast – Very Low Noise - Charged Particle Amplifier

Single Micro Channel Amplifier (Pore ~ 0.002 mm in diameter)

Micro Channel Plate (MCP - Array of pores)

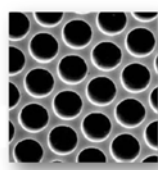
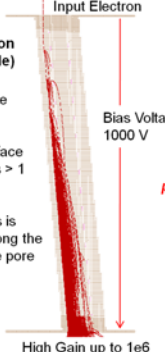
Micro Channel Plate Used In Light Amplification

Amplification (SE Cascade)

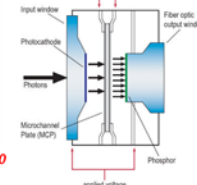
Electrons are accelerated

Strike a surface This creates > 1 electron

The process is repeated along the length of the pore



pore diameter ranges from 5-10 um in with an AR of >50:1



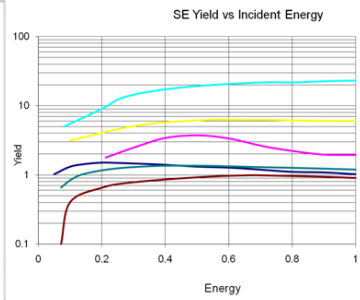
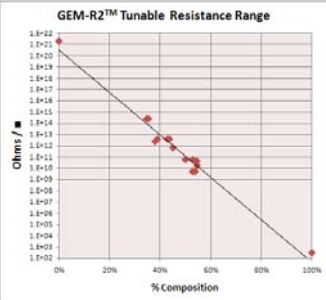
NV Application



High Gain up to  $1e6$   
Low noise – Very fast pico second response

Commercial MCP technology is the result of decades of work with lead-glass, fiber optics, fundamentally unchanged from 1970. Functionalization requires high temperature, hydrogen reduction of the pore surface, forming electrically active, conductive and secondary electron (SE) emissive layers, neither of which can be optimized independently. With the development of ALD nanofilms it is possible to independently tune the MCP mechanical, resistive and emissive properties for very large surface area devices at a fraction of the cost of existing commercial technologies. ALD nanofilm technology is enabling significant opportunities in the Scientific, Medical and Homeland Security market places.

## ALD Nanofilms\*: Conductive & Electron Emissive



### Conductive nanofilms

- Zn doped CuO formed in a nanolaminate structure with alternating layers of  $Al_2O_3$
- Pt nanoclusters formed within an  $Al_2O_3$  nanoalloy

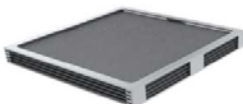
### Emissive nanofilms

- Thin, conductively doped  $Al_2O_3$
- Thin MgO
- Thin MgO –  $TiO_2$  nanolaminate

\*Technology Covered by U.S. Patent Nos. 5,729,244; 6,522,061; 7,408,142; 7,759,138; 7,855,493; 8,052,884; 7,977,617 and 8,134,108 and other Pending U.S. and Foreign Patents.

## Experimental Method: GEMStar-8 ALD Equipment

200mm Square Substrate Holder (holds qty of 5)



GEMStar-8 system is designed for extreme surface area, high aspect ratio structures: Multi-channel precursor delivery system isolates & distributes precursors combine with a tapered exhaust to provide exceptional nanofilm uniformity.

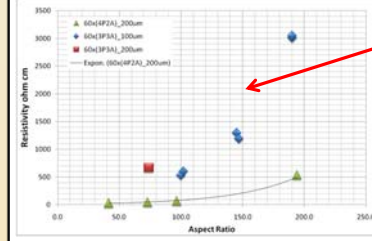
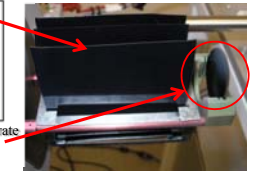
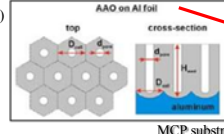
The differentially pumped system seals eliminate gas permeation which along with separate and actively heated Oxidant and Metal-Organic manifolds eliminate parasitic nanofilm production.

Metrology Interface for QCM, ellipsometry, FTIR, OES and room for up to six high capacity precursor cylinders (2 heated) with 2 independent gas lines, maximizes system productivity.

## Experimental Method: Process Development

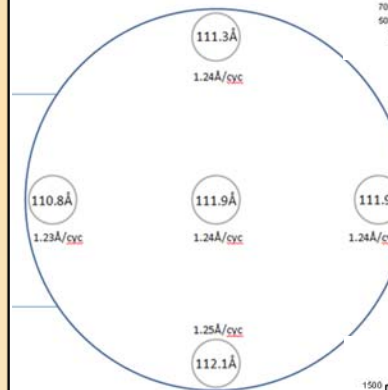
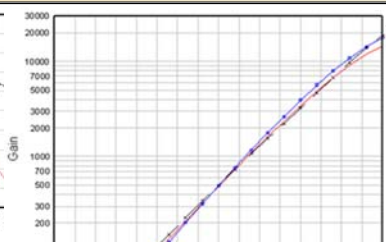
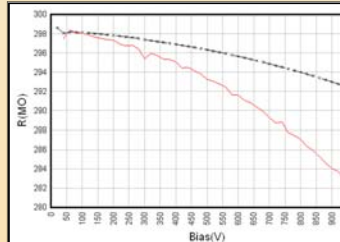
Surface Area Surrogate: (AAO) Anodized Aluminum Oxide:

- 2- sided
- 60mm<sup>2</sup>
- 50nm diameter pores
- 251 nm pore pitch
- 50µm pore thickness



AAO aspect ratio (AR) 300:1 (MCP=60:1)  
• Electrical & process characterization for AR Penetration of conducting film into fiber optic structures of constant diameter & varying length. The resulting resistance measurements demonstrate ALD nanofilm capability for coverage into ARs exceeding 200:1  
• Mechanical assessment, using specialized fiber optics and index matching, optically locating the depth of penetration. Internal fiber diameter (pore width) is 14.9µm and the length of penetration is measured to be 4803µm, resulting in AR coverage of 322:1.

## Results



### Graph Above Left:

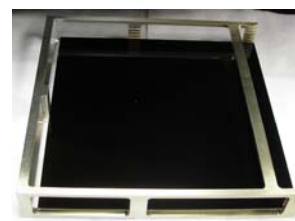
R of AAO surrogate process test MCP.

### Graph Above Right:

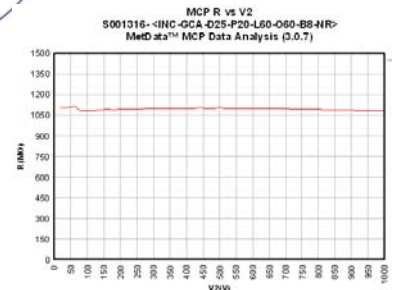
MCP Gain of single & multiple AAO surrogate runs shows equivalent performance of extreme surface area MCP run. All test MCPs: 20um pore, 60:1, 25mm diameter

### Figure Left:

Sample measurements locations and results for 200mm nanofilm uniformity and growth rate test



Fully processed 8" MCP



1 GΩ R of Pilot MCP Processed alongside 8" MCP Provides R of 10 MΩ for 8" equivalent resistance

## Summary

Building on research using conventionally sized MCP devices, MCP performance has been demonstrated using conductive and emissive ALD nanoalloy and nanolaminate films, incorporating surface areas in excess of 8.3 m<sup>2</sup> for MCP devices with aspect ratios in excess of 60:1. In addition to independent tuning of device properties, we have demonstrated capability for film uniformity across a 200mm substrate. These results establish the capability to achieve exceptional MCP device performance (high gain, long lifetime) in the extreme surface area and aspect ratio environment.

## Acknowledgements

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